Low Temperature, Conversion-Free Thermal Atomic Layer Etching of Zinc Oxide using Hydrofluoric Acid and Trimethylgallium

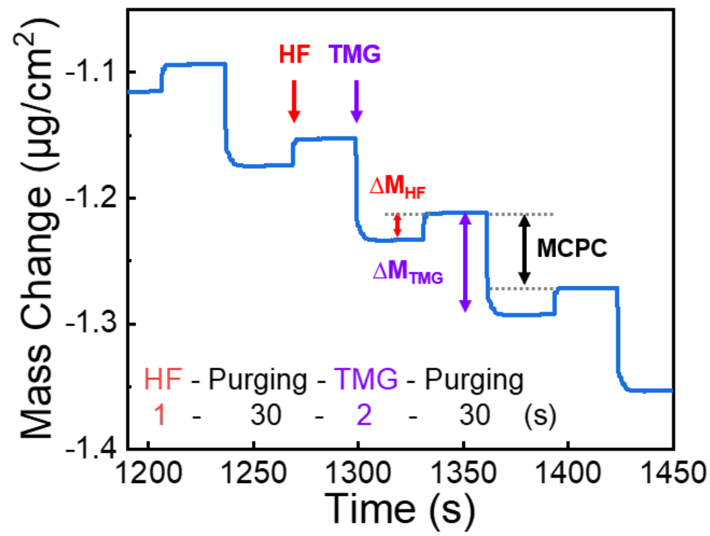

Figure 1. QCM mass change during ZnO ALE using HF and TMG at 100 °C

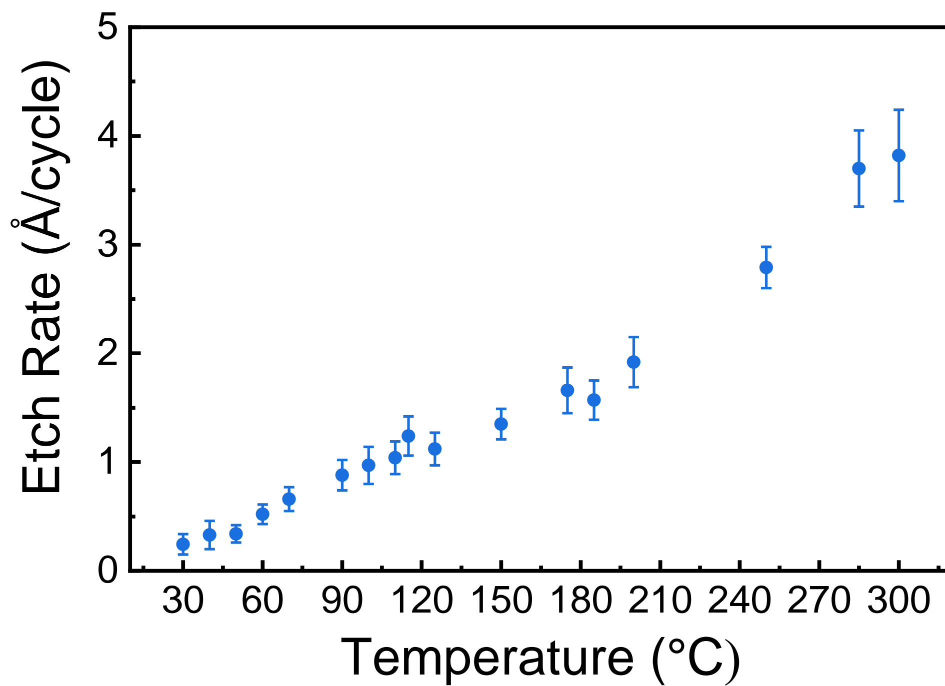

Figure 2. Etch rate of ZnO ALE using HF/TMG versus temperature from 30 to 300 °C.